

Features

- Wide Power Supply Range, 3.0 VDC to 5.5 VDC
- Compatible with JEDEC Standard AT27C512R
- Low Power 3-Volt CMOS Operation
 - 100 μ A max. Standby
 - 26 mW max. Active at 1 MHz for $V_{CC} = 3.3$ VDC
 - 110 mW max. Active at 5 MHz for $V_{CC} = 5.5$ VDC
- Read Access Time - 200 ns
- Wide Selection of JEDEC Standard Packages including OTP
 - 28-Lead, 600-mil Cerdip and OTP Plastic DIP, SOIC or TSOP
 - 32-Pad LCC, 32-Lead JLCC and OTP PLCC
- High Reliability CMOS Technology
 - 2000 V ESD Protection
 - 200 mA Latchup Immunity
- Rapid Programming - 100 μ s/byte (typical)
- Two-line Control
- CMOS and TTL Compatible Inputs and Outputs
- Integrated Product Identification Code
- Commercial and Industrial Temperature Ranges

**512K (64K x 8)
Low Voltage
UV
Erasable
CMOS
EPROM**

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Description

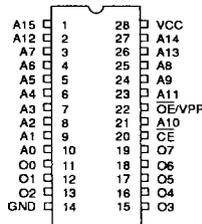
The AT27LV512R chip is a low power, low voltage 524,288 bit Ultraviolet Erasable and Electrically Programmable Read Only Memory (EPROM) organized as 64K x 8 bits. It requires only one supply in the range of 3.0 to 5.5 VDC in normal read mode operation, making it ideal for battery powered systems.

With a typical power draw of only 18 mW at 1 MHz and V_{CC} at 3.3 VDC, the AT27LV512R will draw less than one fifth the power of a standard 5-volt EPROM. Standby mode supply current is typically less than 10 μ A.

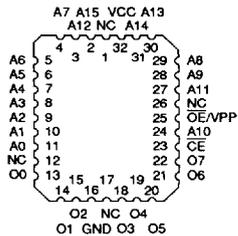
Pin Configurations

Pin Name	Function
A0-A15	Addresses
O0-O7	Outputs
\overline{CE}	Chip Enable
\overline{OE}/V_{PP}	Output Enable
NC	No Connect

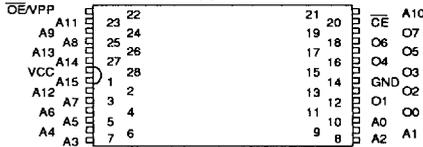
CDIP, PDIP, SOIC Top View



LCC, JLCC, PLCC Top View



TSOP Top View
Type 1



Note: PLCC Package Pins 1 and 17 are DON'T CONNECT.



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Description (Continued)

The AT27LV512R comes in a choice of industry standard JEDEC-approved through hole and surface mount packages including windowed and one time programmable (OTP) packages, such as the OTP thin small outline package (TSOP). All devices feature two line control (\overline{CE} , \overline{OE}) to give designers the flexibility to prevent bus contention.

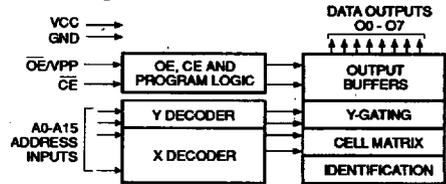
The AT27LV512R operating with V_{CC} at 3.0 VDC produces TTL level outputs that are compatible with standard TTL logic devices operating at $V_{CC} = 5.0$ VDC.

Atmel's 27LV512R has additional features to ensure high quality and efficient production use. The Rapid Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 μ s/byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27LV512R programs identically as an AT27C512R.

Erasure Characteristics

The entire memory array of the AT27LV512R is erased (all outputs read as V_{OH}) after exposure to ultraviolet light at a wavelength of 2537 Å. Complete erasure is assured after a minimum of 20 minutes exposure using 12,000 μ W/cm² intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of 15 W-sec/cm². To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias	-40°C to +85°C
Storage Temperature.....	-65°C to +125°C
Voltage on Any Pin with Respect to Ground.....	-2.0 V to +7.0 V ⁽¹⁾
Voltage on A9 with Respect to Ground	-2.0 V to +14.0 V ⁽¹⁾
V _{PP} Supply Voltage with Respect to Ground.....	-2.0 V to +14.0 V ⁽¹⁾
Integrated UV Erase Dose	7258 W-sec/cm ²

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Notes:

1. Minimum voltage is -0.6 V dc which may undershoot to -2.0 V for pulses of less than 20 ns. Maximum output pin voltage is $V_{CC} + 0.75$ V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0 V for pulses of less than 20 ns.

Operating Modes

Mode \ Pin	\overline{CE}	\overline{OE}/V_{PP}	A _i	V _{CC}	Outputs
Read	V _{IL}	V _{IL}	A _i	V _{CC}	DOUT
Output Disable	V _{IL}	V _{IH}	X ⁽¹⁾	V _{CC}	High Z
Standby	V _{IH}	X	X	V _{CC}	High Z
Rapid Program ⁽²⁾	V _{IL}	V _{PP}	A _i	V _{CC} ⁽²⁾	DIN
PGM Verify ⁽²⁾	V _{IL}	V _{IL}	A _i	V _{CC} ⁽²⁾	DOUT
PGM Inhibit ⁽²⁾	V _{IH}	V _{PP}	X	V _{CC} ⁽²⁾	High Z
Product Identification ^{(2),(4)}	V _{IL}	V _{IL}	A ₉ = V _{IH} ⁽³⁾ A ₀ = V _{IH} or V _{IL} A ₁ -A ₁₅ = V _{IL}	V _{CC} ⁽²⁾	Identification Code

- Notes:
1. X can be V_{IL} or V_{IH}.
 2. Refer to Programming characteristics. Programming modes require $V_{CC} > 4.5$ V.
 3. V_H = 12.0 ± 0.5 V.

4. Two identifier bytes may be selected. All A_i inputs are held low (V_{IL}), except A₉ which is set to V_H and A₀ which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

D.C. and A.C. Operating Conditions for Read Operation

		AT27LV512R	
		-20	-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C
V _{CC} Power Supply		3.0 V to 5.5 V	3.0 V to 5.5 V

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D.C. and Operating Characteristics for Read Operation

(V_{CC} = 3.0 V to 5.5 V unless otherwise specified)

Symbol	Parameter	Condition	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = -0.1 V to V _{CC} +1 V		10	μA
I _{LO}	Output Leakage Current	V _{OUT} = -0.1 V to V _{CC} +0.1 V		10	μA
I _{SB}	V _{CC} ⁽¹⁾ Standby Current	I _{SB1} (CMOS), CE = V _{CC} -0.3 to V _{CC} +1.0 V		100	μA
		I _{SB2} (TTL), CE = 2.0 to V _{CC} +1.0 V		1	mA
I _{CC}	V _{CC} Active Current	I _{CC1} f = 5 MHz, I _{OUT} = 0 mA, CE = V _{IL} , V _{CC} = 5.5 V	Com.	20	mA
			Ind.	25	mA
		I _{CC2} f = 1 MHz, I _{OUT} = 0 mA CE = V _{IL} , V _{CC} = 3.3 V	Com.	8	mA
			Ind.	10	mA
V _{IL}	Input Low Voltage		-0.6	0.8	V
V _{IH}	Input High Voltage		2.0	V _{CC} +0.75	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA		.45	V
V _{OH}	Output High Voltage	I _{OH} = -100 μA		V _{CC} -0.3	V
		I _{OH} = -400 μA		2.4	V

Notes: 1. V_{CC} must be applied simultaneously or before OE/V_{PP}, and removed simultaneously or after OE/V_{PP}.

A.C. Characteristics for Read Operation (V_{CC} = 3.0 V to 5.5 V)

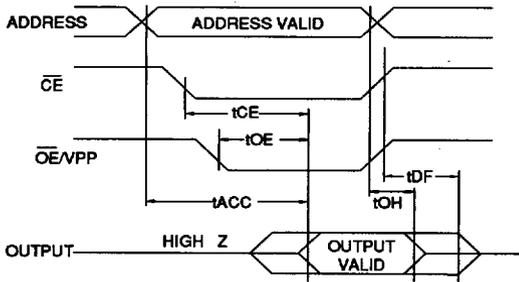
		AT27LV512R				Units	
		-20		-25			
Symbol	Parameter	Condition		Min	Max	Min	Max
t _{ACC} ⁽³⁾	Address to Output Delay	CE = OE/V _{PP} = V _{IL}	Com.	200		250	ns
			Ind.	200		250	ns
t _{CE} ⁽²⁾	CE to Output Delay	OE/V _{PP} = V _{IL}		200		250	ns
t _{OE} ^(2,3)	OE/V _{PP} to Output Delay	CE = V _{IL}		70		100	ns
t _{DF} ^(4,5)	OE/V _{PP} High to Output Float	CE = V _{IL}		50		50	ns
t _{OH}	Output Hold from Address, CE or OE/V _{PP} , whichever occurred first	CE = OE/V _{PP} = V _{IL}		0		0	ns

Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.



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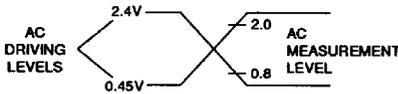
A.C. Waveforms for Read Operation ⁽¹⁾



Notes:

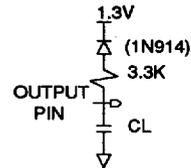
1. Timing measurement references are 0.8 V and 2.0 V. Input AC driving levels are 0.45 V and 2.4 V. See Input Test Waveforms and Measurement Levels.
2. \overline{OE}/V_{PP} may be delayed up to $t_{CE}-t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE} .
3. \overline{OE}/V_{PP} may be delayed up to $t_{ACC}-t_{OE}$ after the address is valid without impact on t_{ACC} .
4. This parameter is only sampled and is not 100% tested.
5. Output float is defined as the point when data is no longer driven.

Input Test Waveforms and Measurement Levels



$t_R, t_F < 20$ ns (10% to 90%)

Output Test Load



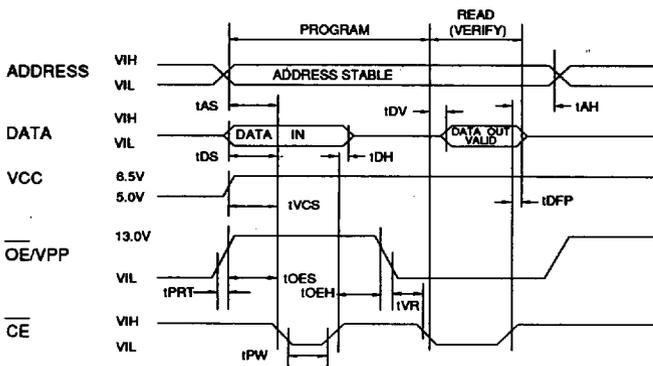
Note: $C_L = 100$ pF including jig capacitance.

Pin Capacitance ($f = 1$ MHz, $T = 25^\circ\text{C}$) ⁽¹⁾

	Typ	Max	Units	Conditions
C_{IN}	4	8	pF	$V_{IN} = 0$ V
C_{OUT}	8	12	pF	$V_{OUT} = 0$ V

Notes: 1. Typical values for 5-V supply voltage. This parameter is only sampled and is not 100% tested.

Programming Waveforms ⁽¹⁾



Notes:

1. The Input Timing Reference is 0.8 V for V_{IL} and 2.0 V for V_{IH} .
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.

D.C. Programming Characteristics

$T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.5 \pm 0.25\text{ V}$, $\overline{OE}/V_{PP} = 13.0 \pm 0.25\text{ V}$

Sym- bol	Parameter	Test Conditions	Limits		Units
			Min	Max	
I _{LI}	Input Load Current	$V_{IN} = V_{IL}, V_{IH}$		10	μA
V _{IL}	Input Low Level	(All Inputs)	-0.6	0.8	V
V _{IH}	Input High Level		2.0	$V_{CC}+1$	V
V _{OL}	Output Low Volt.	$I_{OL} = 2.1\text{ mA}$.45	V
V _{OH}	Output High Volt.	$I_{OH} = -400\ \mu\text{A}$	2.4		V
I _{CC2}	V _{CC} Supply Current (Program and Verify)			25	mA
I _{PP2}	\overline{OE}/V_{PP} Current	$\overline{CE} = V_{IL}$		25	mA
V _{ID}	A9 Product Identification Voltage		11.5	12.5	V

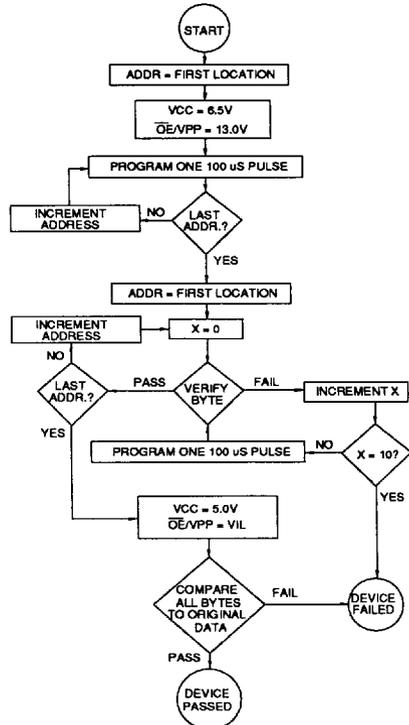
Atmel's 27LV512R Integrated Product Identification Code⁽¹⁾

Codes	Pins									Hex Data
	A0	O7	O6	O5	O4	O3	O2	O1	O0	
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	0	0	0	0	1	1	0	1	0D

Note: 1. The AT27LV512R has the same Product Identification Code as the AT27C512R. Both are programming compatible.

Rapid Programming Algorithm

A 100 μs \overline{CE} pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5 V and \overline{OE}/V_{PP} is raised to 13.0 V. Each address is first programmed with one 100 μs \overline{CE} pulse without verification. Then a verification/reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 μs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. \overline{OE}/V_{PP} is then lowered to V_{IL} and V_{CC} to 5.0 V. All bytes are read again and compared with the original data to determine if the device passes or fails.



A.C. Programming Characteristics

$T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.5 \pm 0.25\text{ V}$, $\overline{OE}/V_{PP} = 13.0 \pm 0.25\text{ V}$

Sym- bol	Parameter	Test Conditions* (see Note 1)	Limits		Units
			Min	Max	
t _{AS}	Address Setup Time		2		μs
t _{OES}	\overline{OE}/V_{PP} Setup Time		2		μs
t _{OEH}	\overline{OE}/V_{PP} Hold Time		2		μs
t _{DS}	Data Setup Time		2		μs
t _{AH}	Address Hold Time		0		μs
t _{DH}	Data Hold Time		2		μs
t _{DFP}	\overline{CE} High to Output Float Delay	(Note 2)	0	130	ns
t _{VCS}	V _{CC} Setup Time		2		μs
t _{PW}	\overline{CE} Program Pulse Width	(Note 3)	95	105	μs
t _{DV}	Data Valid from \overline{CE}	(Note 2)	1		μs
t _{VR}	\overline{OE}/V_{PP} Recovery Time		2		μs
t _{PRT}	\overline{OE}/V_{PP} Pulse Rise Time During Programming		50		ns

*A.C. Conditions of Test:

Input Rise and Fall Times (10% to 90%) 20 ns
 Input Pulse Levels 0.45 V to 2.4 V
 Input Timing Reference Level 0.8 V to 2.0 V
 Output Timing Reference Level 0.8 V to 2.0 V

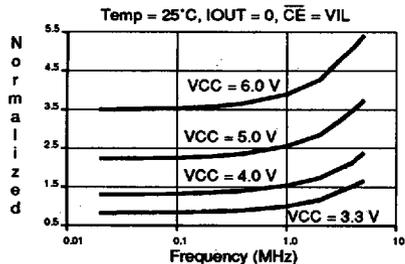
Notes:

1. V_{CC} must be applied simultaneously or before \overline{OE}/V_{PP} and removed simultaneously or after \overline{OE}/V_{PP} .
2. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram.
3. Program Pulse width tolerance is 100 $\mu\text{sec} \pm 5\%$.

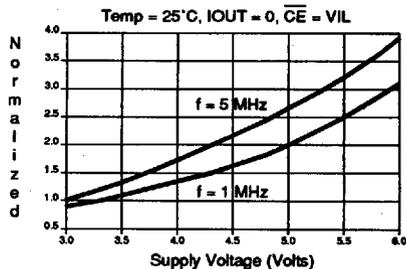


LV EPROM Product Characteristics

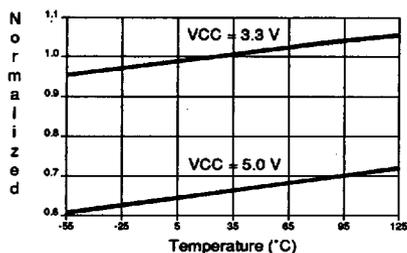
NORMALIZED SUPPLY CURRENT vs. FREQUENCY



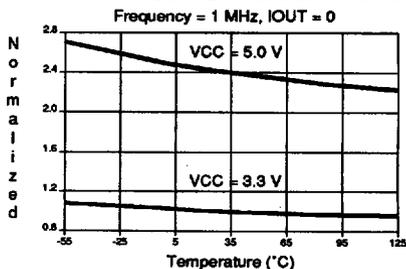
NORMALIZED SUPPLY CURRENT vs. VOLTAGE



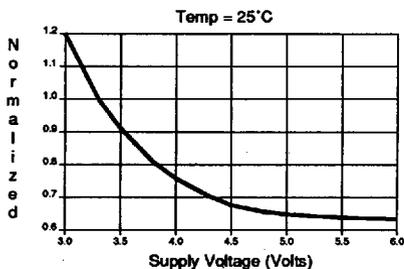
NORMALIZED ACCESS TIME vs. TEMPERATURE



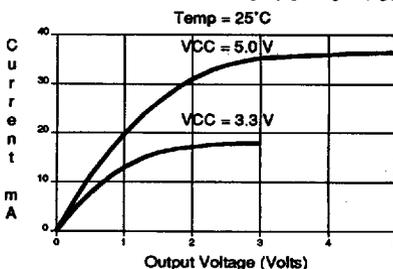
NORMALIZED SUPPLY CURRENT vs. TEMP.



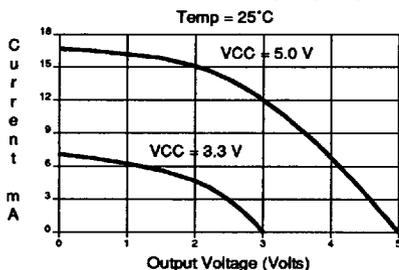
NORMALIZED ACCESS TIME vs. SUPPLY VOLTAGE



OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE



OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



Ordering Information

t _{ACC} (ns)	I _{CC} (mA) V _{CC} = 3.3 V		Ordering Code	Package	Operation Range
	Active	Standby			
200	8	0.1	AT27LV512R-20DC AT27LV512R-20JC AT27LV512R-20KC AT27LV512R-20LC AT27LV512R-20PC AT27LV512R-20RC	28DW6 32J 32KW 32LW 28P6 28R	Commercial (0°C to 70°C)
200	10	0.1	AT27LV512R-20DI AT27LV512R-20KI AT27LV512R-20LI	28DW6 32KW 32LW	Industrial (-40°C to 85°C)
250	8	0.1	AT27LV512R-25DC AT27LV512R-25JC AT27LV512R-25KC AT27LV512R-25LC AT27LV512R-25PC AT27LV512R-25RC	28DW6 32J 32KW 32LW 28P6 28R	Commercial (0°C to 70°C)
250	10	0.1	AT27LV512R-25DI AT27LV512R-25KI AT27LV512R-25LI	28DW6 32KW 32LW	Industrial (-40°C to 85°C)

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t _{ACC} (ns)	I _{CC} (mA) V _{CC} = 3.3 V		Ordering Code	Package	Operation Range
	Active	Standby			
200	8	0.1	AT27LV512R-20TC	28T	Commercial (0° to 70°C)
250	8	0.1	AT27LV512R-25TC	28T	Commercial (0° to 70°C)

Package Type	
28DW6	28 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)
32KW	32 Lead, Windowed, Ceramic J-Leaded Chip Carrier (JLCC)
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)
28R	28 Lead, 0.330" Wide, Plastic Gull Wing Small Outline OTP (SOIC)
28T	28 Lead, Plastic Thin Small Outline Package OTP (TSOP)



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